







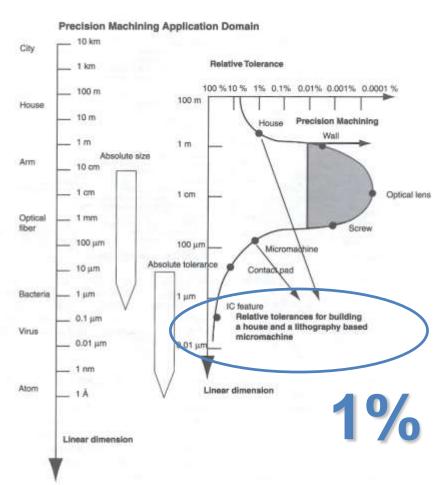
Nanofabrication technologies for nanophotonics

Igor Ozerov

Aix-Marseille Univ, CNRS, CINaM 13288 Marseille France



Relative precision of nanofabrication



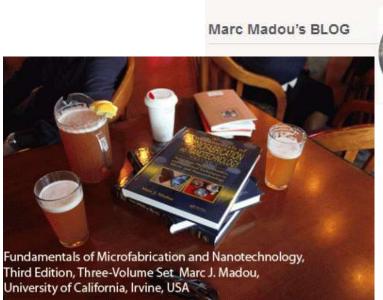
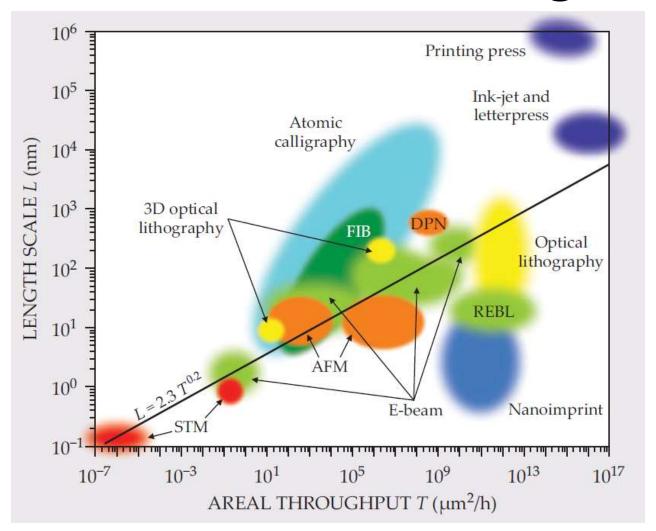


Image: M. Madou, 'Fundamentals of microfabrication'

Application field for precision machining in terms of absolute sizes and absolute and relative tolerances.

Fundamentals of Microfabrication

Nanomanufacturing

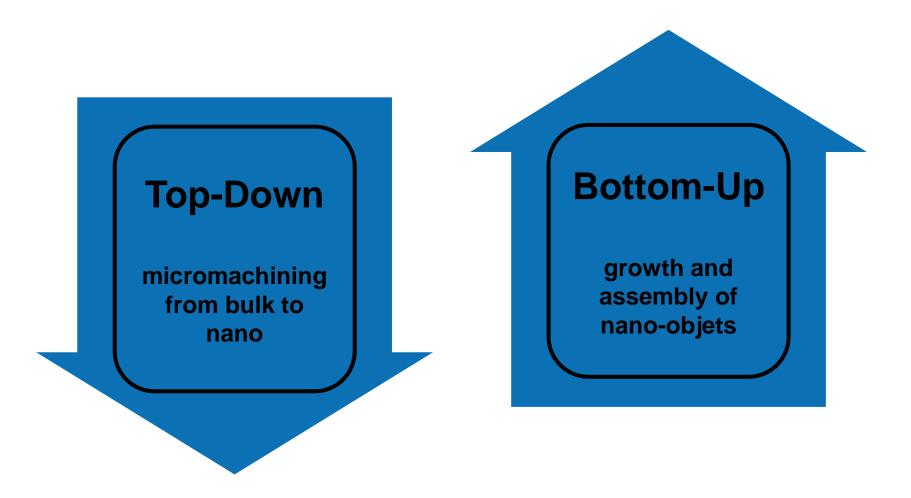


Imboden and Bishop, **Top-down nanomanufacturing**, Physics Today **67**, 45 (2014)

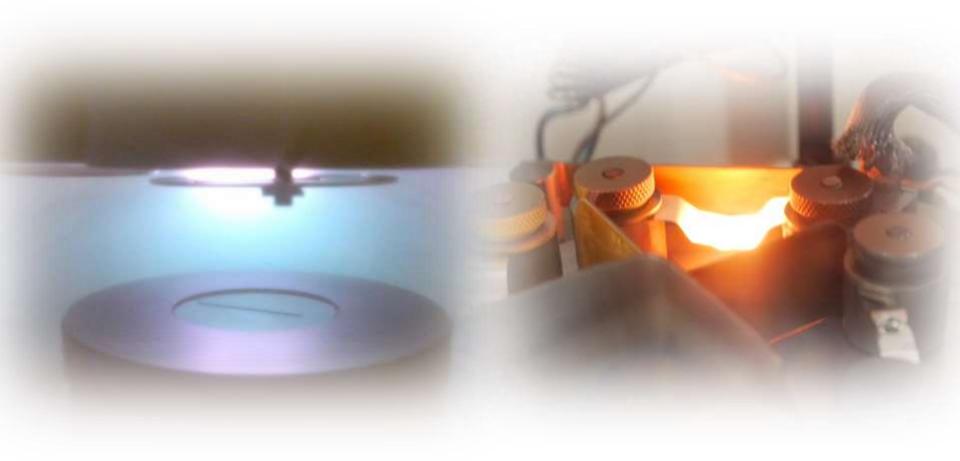
Plan

- Introduction (top-down processes)
 - Deposition
 - Etching
 - Lithography
 - Focused electron and ion beam tecniques
- Exemples plasmonic
- Exemples chiral structures
- Dielectric photonics, silicon
- Exemples, coloration
- Nanosphere lithography (bottom-up)
- Laser-driven methods
- Nanofabrication using vortex beams

Nano- et micro- fabrication approaches



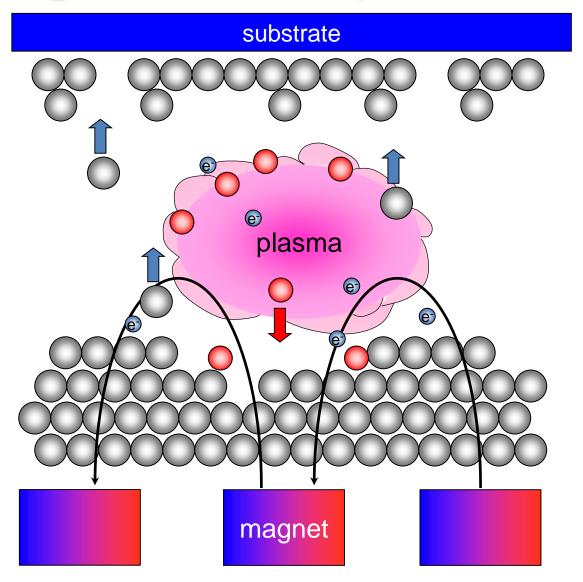
Deposition (additive technics)



Magnetron sputtering (Al, Cr, Ti & W)
Reactive sputtering (nitrides and oxides)
in gas environment

Evaporation (Ag, Al, Au, Cr, Cu & Ni) in vacuum

Magnetron Sputtering



Step coverage in sputtering and evaporation deposition



Figure 7.17 (a) Gap filling with conformal step coverage. (b) Conformal deposition of a larger gap with the same process does not lead to gap filling but the original step height remains. (c) Void and (d) cusp are formed when step coverage is maximum at the step corner

S. Franssila, Introduction to Micro Fabrication. Wiley, 2004.

Nanocones by Directional Evaporation

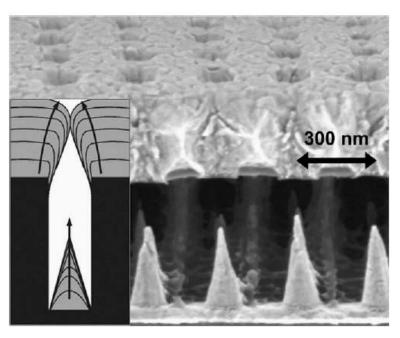
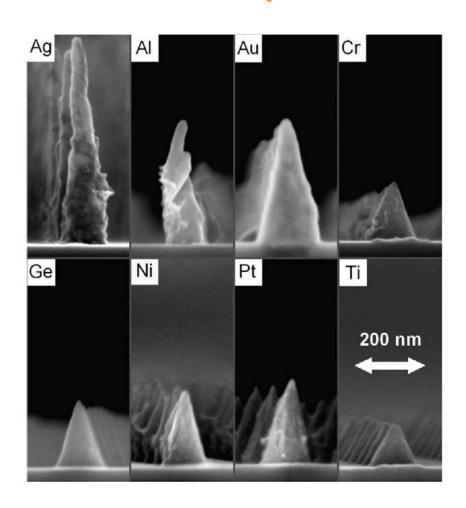
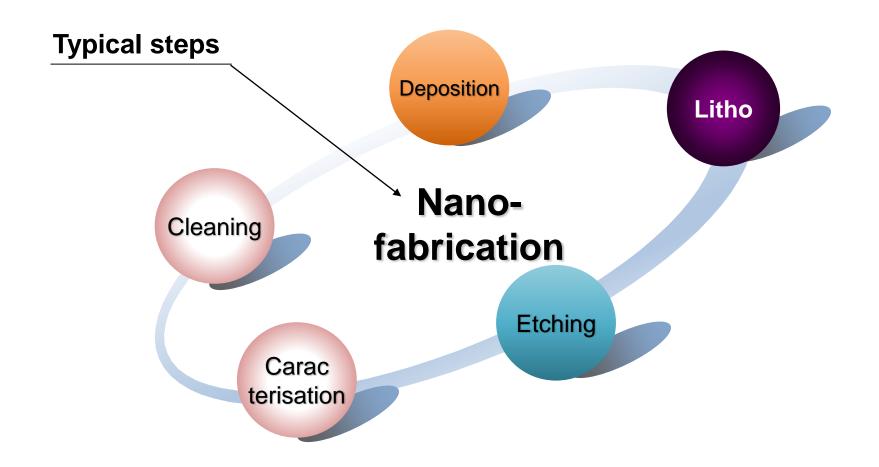


Fig. 3. An SEM image of a sectional view of the structure upon gold evaporation before lift-off. The conical shape is formed spontaneously when the holes in the mask shrink during evaporation (inset). The arrows mark the growth direction of the Au layer.

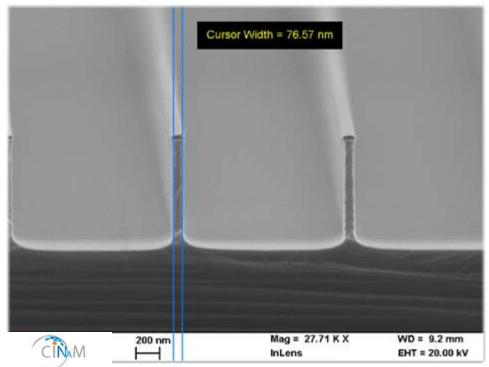


J.M. Kontio et al. / Microelectronic Engineering 87 (2010) 1711–1715

Top-Down Approach

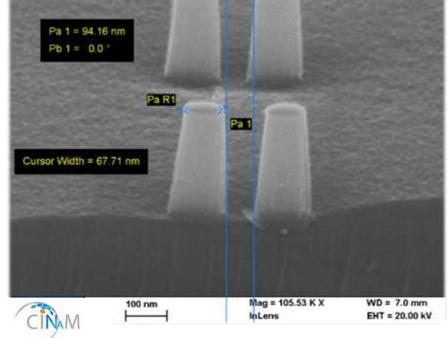


Dry Plasma and Wet Etching

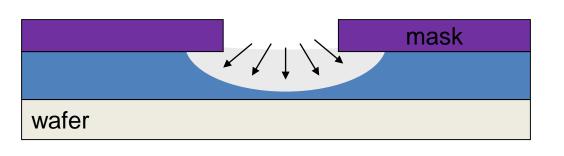


High aspect ratio reactive ion etching of silicon

Wet Chemical Etching
Reactive Ion Etching (RIE) by Plasma
gases: CHF₃ SF₆ O₂
materials: Si SiO₂ Si₃N₄ TiO₂ WO₃
Capacitively (CCP) and
Inductively coupled plasma (ICP)
Argon ion milling

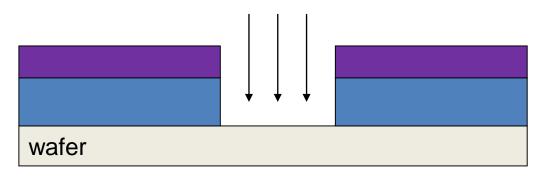


Dry Plasma and Wet Etching



Isotropic

(Example wet : Au in KI₃)

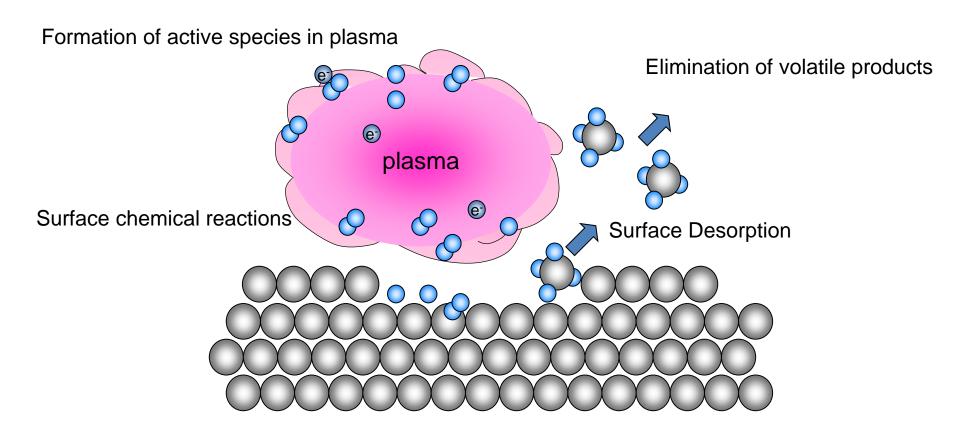


Anisotropic

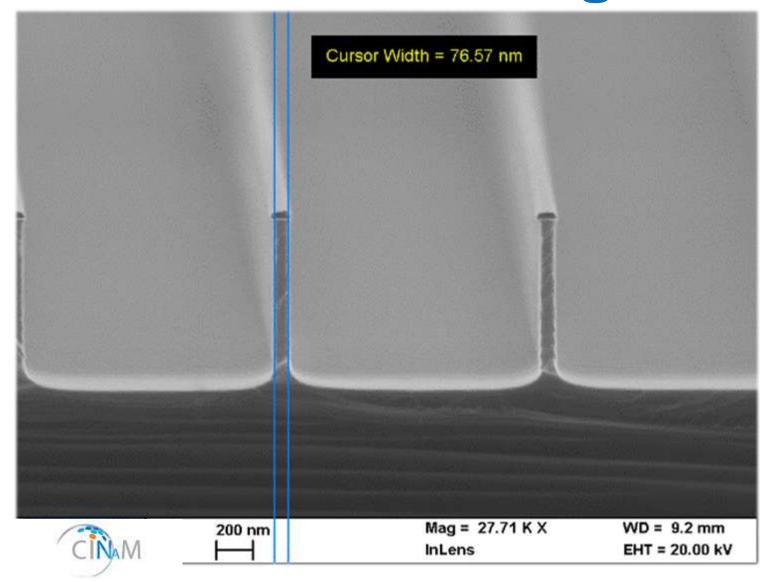
Example wet: Si in KOH

Example dry: Si by SF₆:O₂

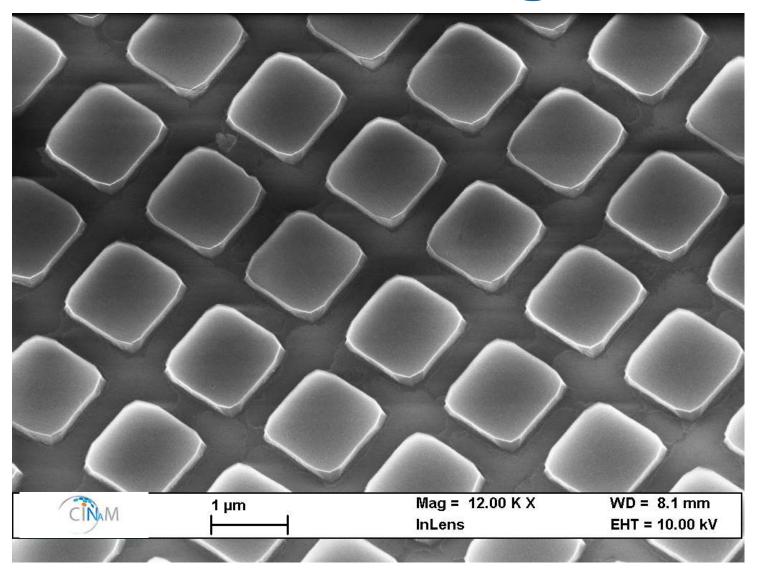
Reactive Ion Etching



Reactive Ion Etching of Si



Alcaline Wet Etching of Silicon

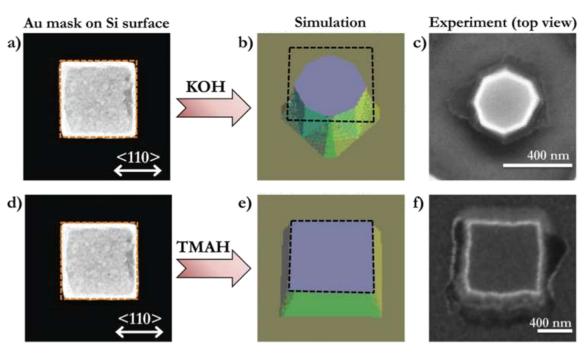


Crystalline silicon nanostructures

KOH or TMAH?

KOH {110}>{100}>{111}

TMAH {100}>{110}>{111}

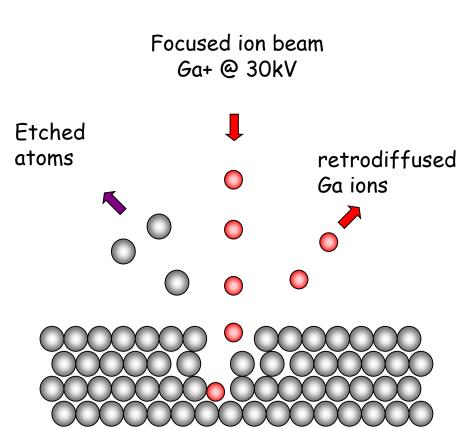


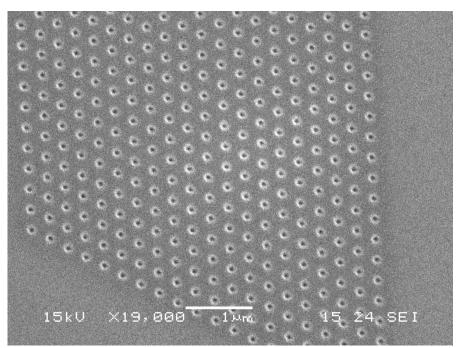
Selective chemical etching, Cr/Au mask



J. Proust, F. Bedu, S. Chenot, I. Soumahoro, I. Ozerov, B. Gallas, R. Abdeddaim, and N. Bonod, Advanced Optical Materials, vol. 3, pp. 1280-1286, 2015.

Focused Ion Beam Milling

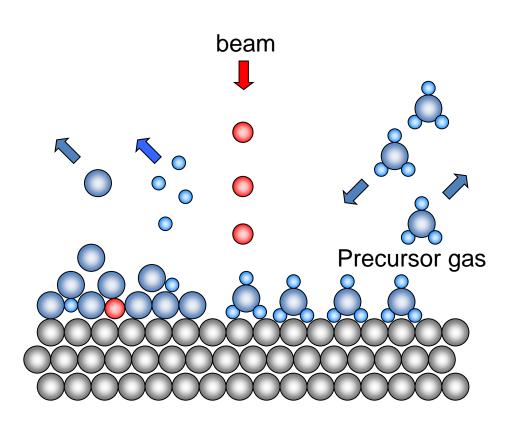


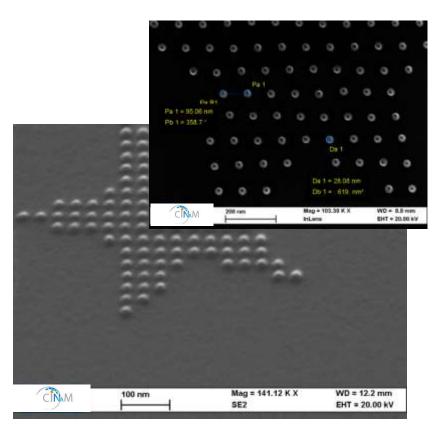


Nanohole array in a SiC crystal

Images: Frédéric BEDU

Local Focused Ion Beam (FIBID) and Electron Beam Induced Deposition (EBID)



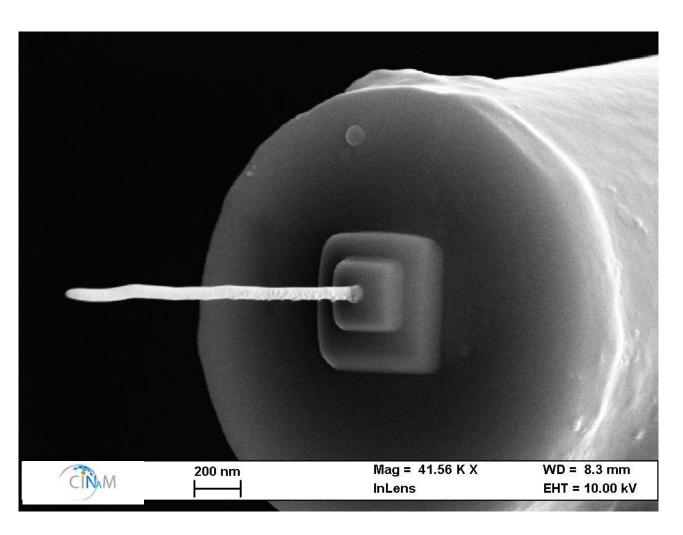


Tungsten nanodots deposition (EBID)

Local Electron Beam Induced Deposition (EBID)

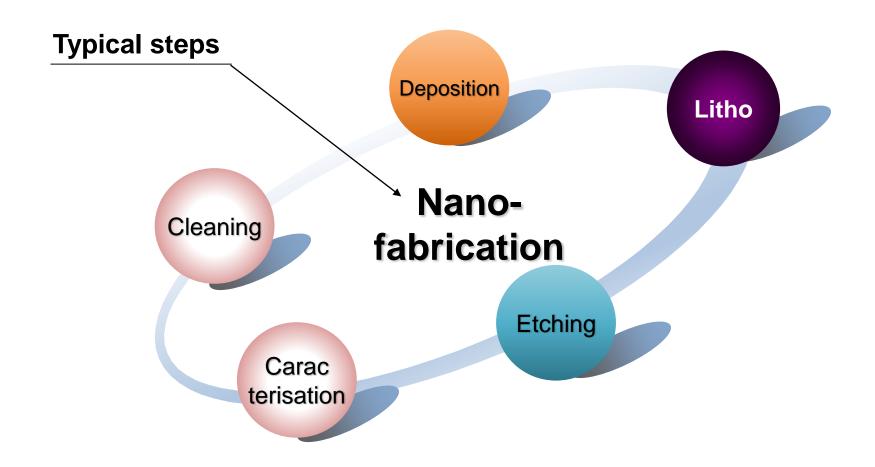


W nanowire

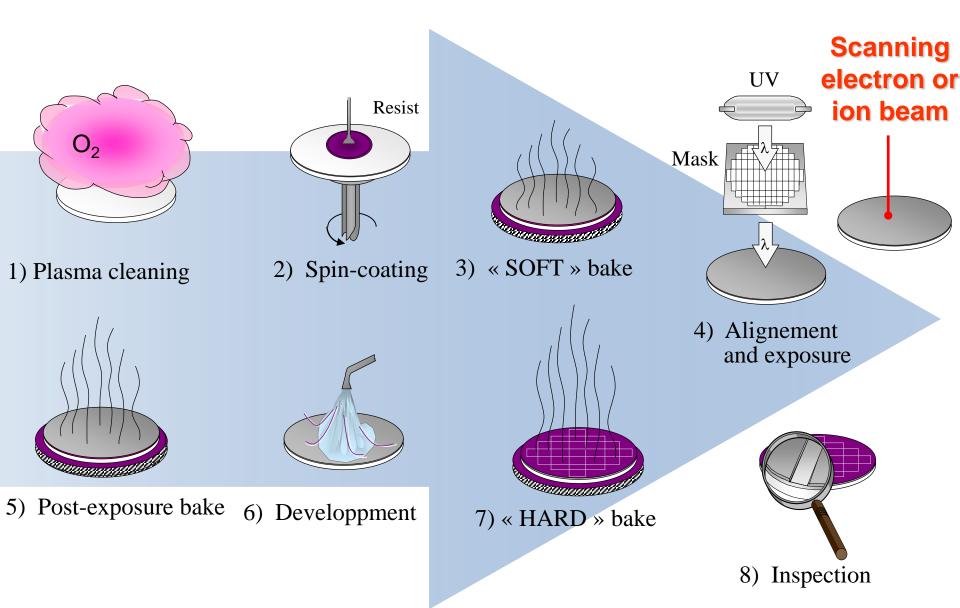


Courtesy Frédéric Bedu and Marion Descoins

Top-Down Approach



UV and e-beam lithography





Electron beam lithography

System Pioneer





Field Emission Gun (FEG) 2nm
Laser interferometer Stage
Stitching and Alignement <50nm
Autofocus system
Gas injection system



Gas Injection System (Orsay physics)









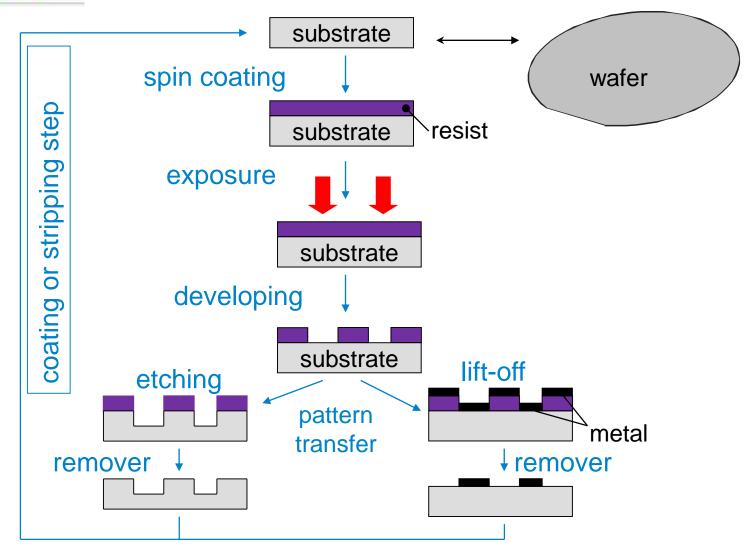






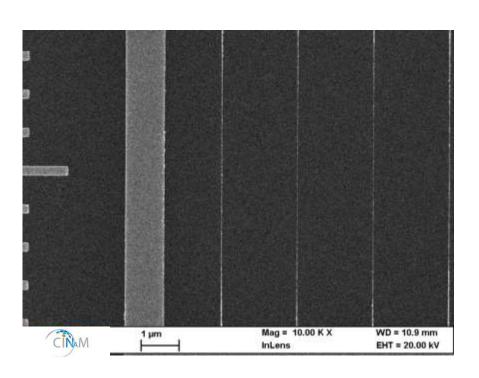


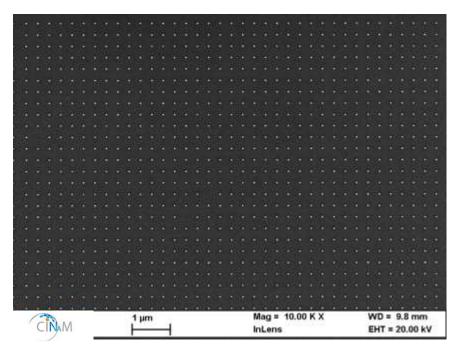
Process technology





Electron beam lithography





Metal lines

(width < 20 nm)

Metal nanodots Cr/Au

(diameter < 50 nm)

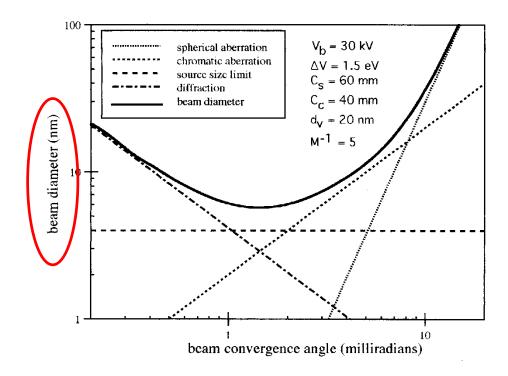
High resolution e-beam lithography + lift off process

Images: Frédéric BEDU



Resolution

- ⇒ De Broglie wavelength at 1 kV: 0.0387 nm
- ⇒ current resolution limit of electron optics is in the range 1 2 nm



SPIE Handbook of Microlithography

Extreme resolution of EBL



pubs.acs.org/NanoLett

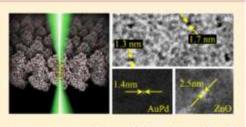
Aberration-Corrected Electron Beam Lithography at the One Nanometer Length Scale

Vitor R. Manfrinato,[†] Aaron Stein, Lihua Zhang, Chang-Yong Nam, ^{†⊚} Kevin G. Yager, [†] Eric A. Stach, ** 100 and Charles T. Black ** 1

Center for Functional Nanomaterials, Brookhaven National Laboratory, Upton, New York 11973-5000, United States

Supporting Information

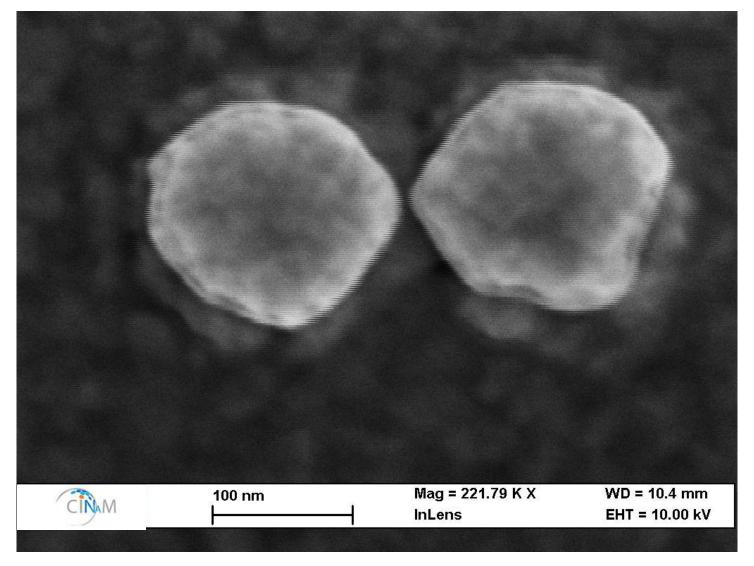
ABSTRACT: Patterning materials efficiently at the smallest length scales is a longstanding challenge in nanotechnology. Electron-beam lithography (EBL) is the primary method for patterning arbitrary features, but EBL has not reliably provided sub-4 nm patterns. The few competing techniques that have achieved this resolution are orders of magnitude slower than EBL. In this work, we employed an aberration-corrected scanning transmission electron microscope for lithography to achieve unprecedented resolution. Here we show aberrationcorrected EBL at the one nanometer length scale using poly(methyl



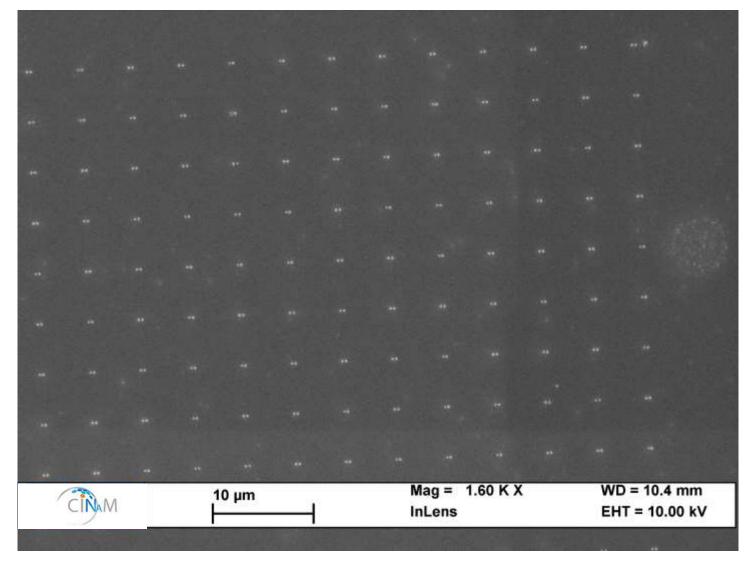
methacrylate) (PMMA) and have produced both the smallest isolated feature in any conventional resist (1.7 ± 0.5 nm) and the highest density patterns in PMMA (10.7 nm pitch for negative-tone and 17.5 nm pitch for positive-tone PMMA). We also demonstrate pattern transfer from the resist to semiconductor and metallic materials at the sub-5 nm scale. These results indicate that polymer-based nanofabrication can achieve feature sizes comparable to the Kuhn length of PMMA and ten times smaller than its radius of gyration. Use of aberration-corrected EBL will increase the resolution, speed, and complexity in nanomaterial fabrication.

KEYWORDS: Nanofabrication, electron-beam lithography, aberration correction, electron microscopy, nanomaterials, pattern transfer, poly(methyl methacrylate)

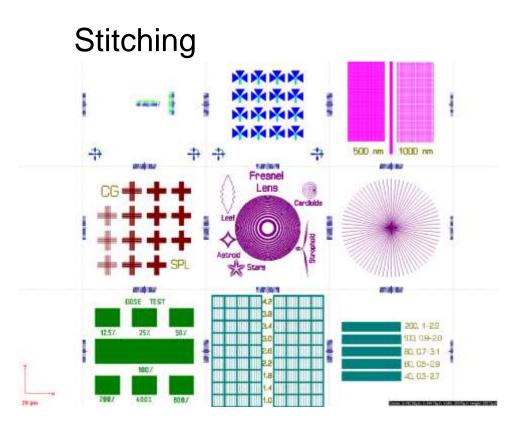
Resolution of EBL



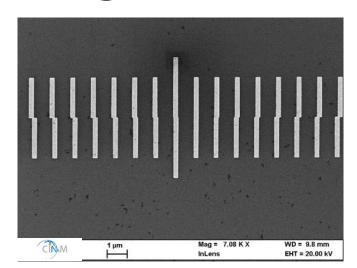
Resolution of EBL

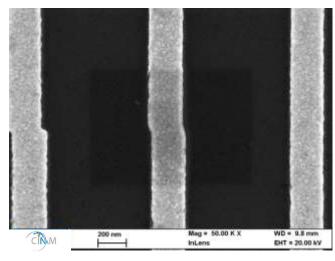


Large area e-beam lithography?



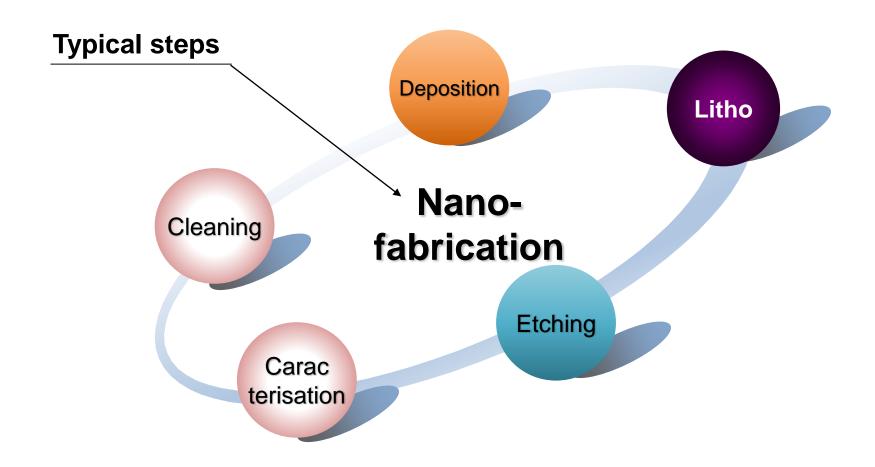
Working Area 300x300µm Write field 100µm





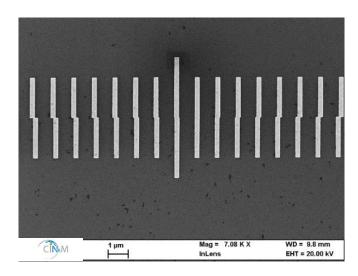
Displacement precision 20 nm (Working Area 900µm)

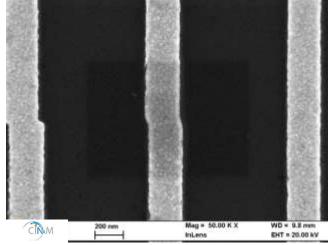
Top-Down Approach



Alignment of two layers using e-beam lithography





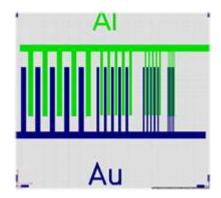


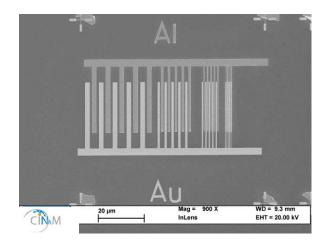
Interferometric movement control (better than 20 nm)

Alignment of two layers using e-beam lithography

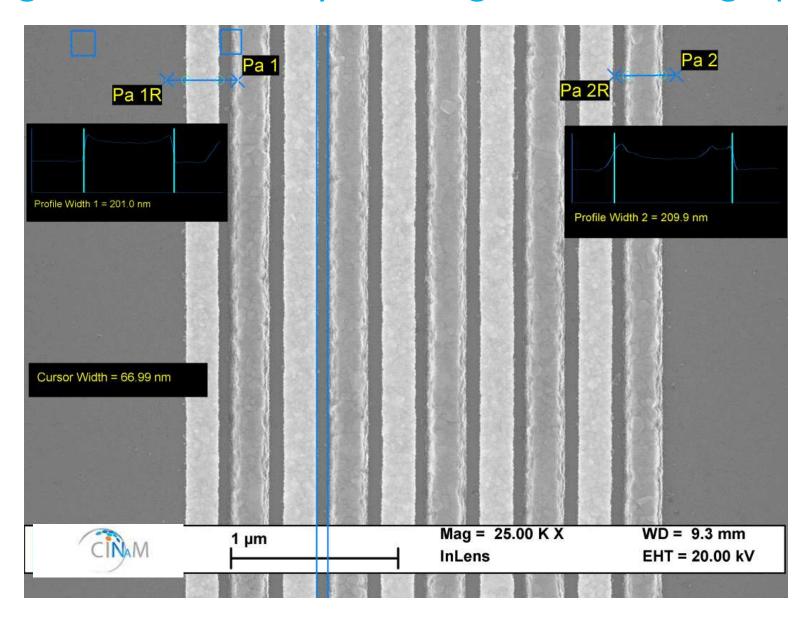
Process steps:

- ☐ Feature design
- □ 1st Resist Spin-coating
- ☐ E-beam exposure
- Development
- ☐ Gold deposition
- ☐ Lift-off
- ☐ 2nd Resist Spin-coating
- □ Alignement
- □ E-beam exposure
- □ Development
- ☐ Aluminum deposition
- ☐ Lift-off

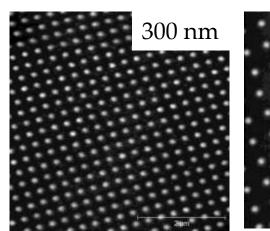


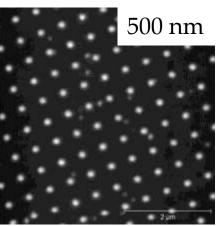


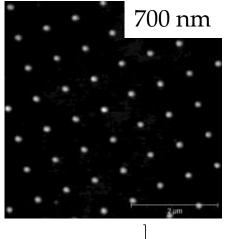
Alignment of two layers using e-beam lithography



Example: Indirect Humidity Sensor

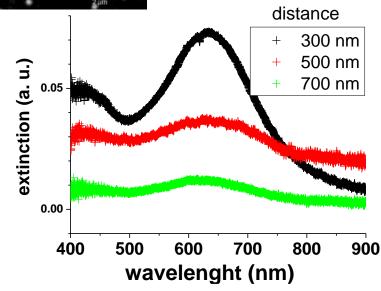






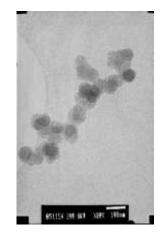
tapping mode topographical AFM images of gold nanodisks respectively with d = 300 nm, d = 500 nm, d = 700 nm. On the right: LSPR signals corresponding to these different samples.



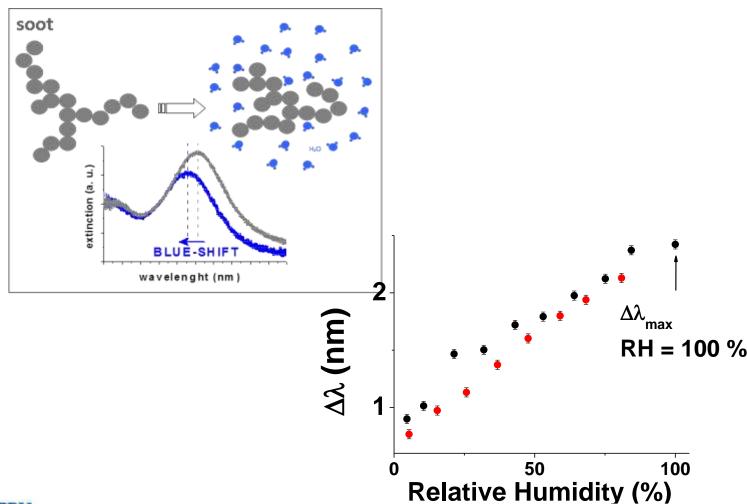


B. Demirdjian, F. Bedu, A. Ranguis, I. Ozerov, A. Karapetyan and C.R. Henry, JPCL 2015

Example: Indirect Humidity Sensor



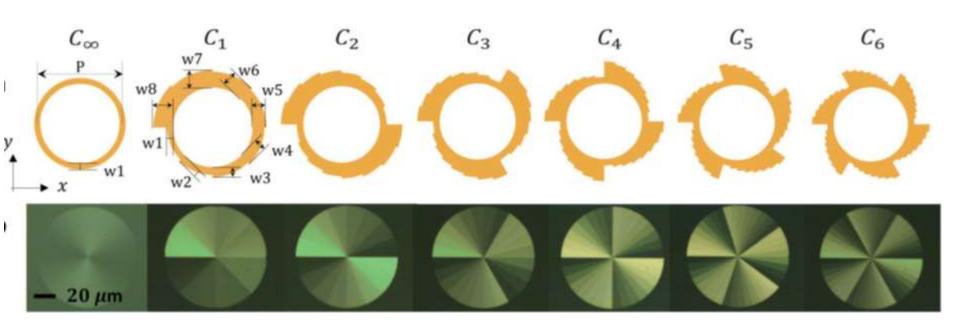
TEM image of the soot particles





B. Demirdjian, F. Bedu, A. Ranguis, I. Ozerov, A. Karapetyan and C.R. Henry, JPCL 2015

Example: Cyclic Group Symmetric Metamaterial for Spin-Orbital Interaction of Light



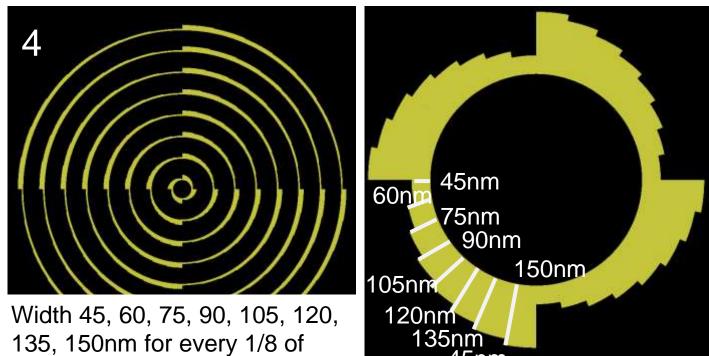
Tapered arc antennas

YU Lee, I Ozerov, F Bedu, JS Kim, F Fages and JW Wu

arXiv:1607.04806



Example: Cyclic Group Symmetric Metamaterial for Spin-Orbital Interaction of Light



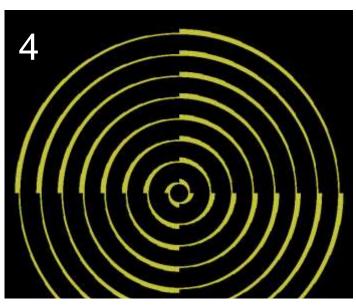
2pi/4

YU Lee, I Ozerov, F Bedu, JS Kim, F Fages and JW Wu

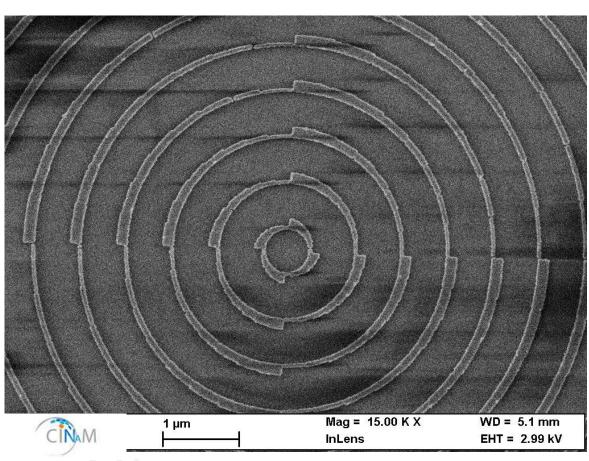
arXiv:1607.04806



Example: Cyclic Group Symmetric Metamaterial for Spin-Orbital Interaction of Light



Width 45, 60, 75, 90, 105, 120, 135, 150nm for every 1/8 of 2pi/4



YU Lee, I Ozerov, F Bedu, JS Kim, F Fages and JW Wu arXiv:1607.04806

The quest for better materials and fabrication techniques

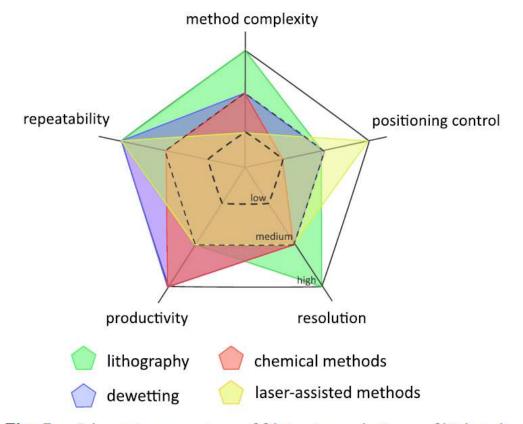


Fig. 5. Schematic comparison of fabrication techniques of high-index nanostructures.

2017 BARANOV, ZUEV, LEPESHOV, KOTOV, KRASNOK, EVLYUKHIN & CHICHKOV

Review Article

Soft UV Nanoimprint Lithography

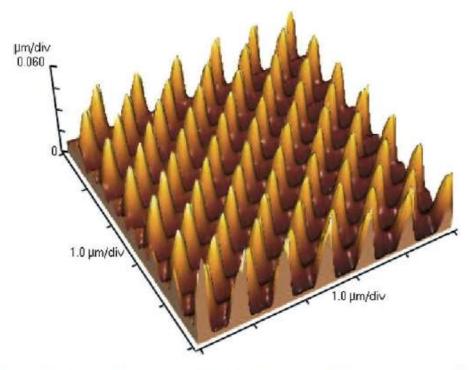


Fig. 2. AFM image of the dots in H-PDMS stamp (periodicity: ~ 500 nm, height: 150 nm, diameter (FWHM): 160 nm).

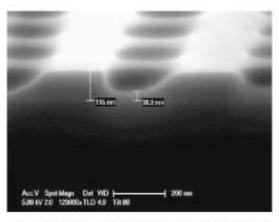


Fig. 3. SEM image of imprint in AMONIL with a PMMA underlayer.

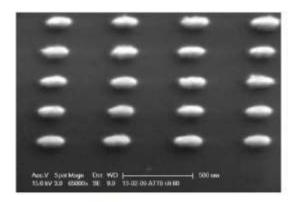


Fig. 4. SEM image of gold nanoparticles after annealing (diameter: ~ 165 nm, periodicity: 500 nm).

G. Barbillon et al. / Microelectronic Engineering 87 (2010) 1001–1004

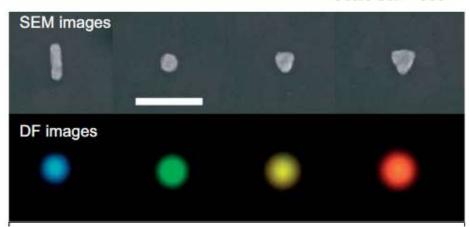
Nanofabrication for highresolution color printing

W. A. Murray, W. L. Barnes/Plasmonic Materials



2007, 19, 3771–3782

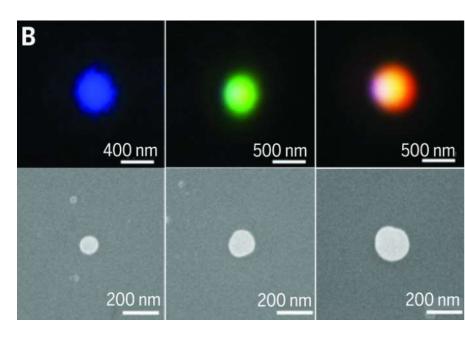
Scale bar = 300



Metallic plasmonic particles

Resonant dielectric nanostructures

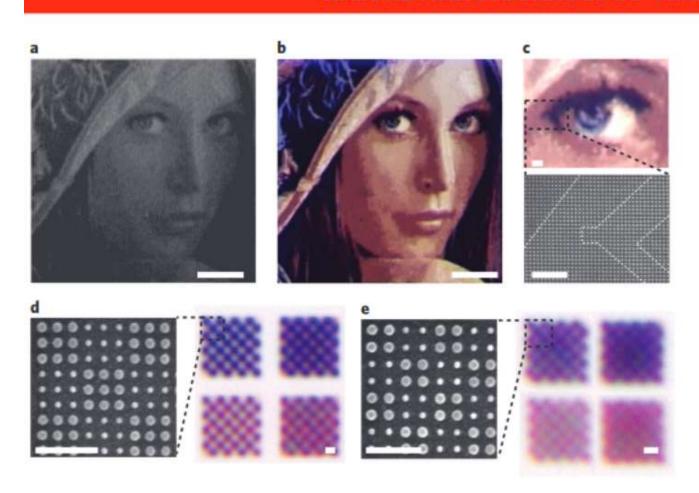
Kuznetsov, Miroshnichenko, Brongersma, Kivshar & Luk'yanchuk, Science 2016



The color is controlled by the shape and the size of nanostructures

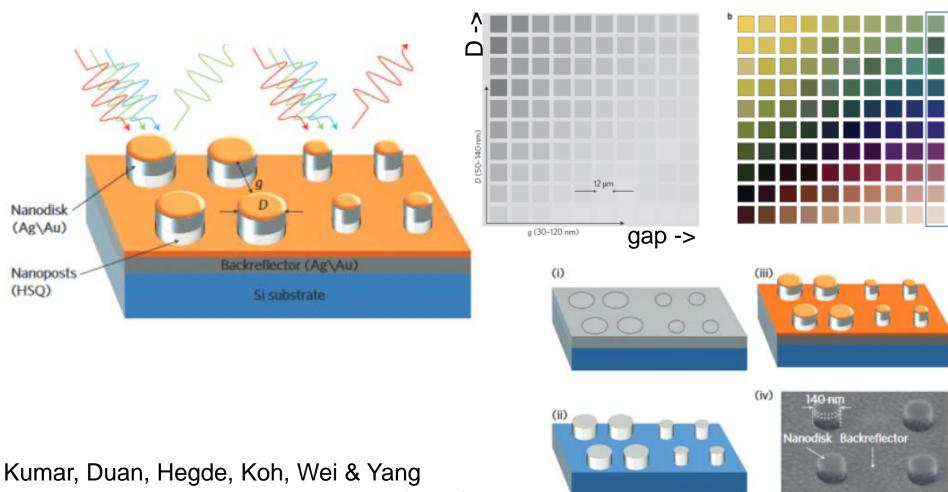
Plasmonic color printing

NATURE NANOTECHNOLOGY DOI: 10.1038/NNANO.2012.128



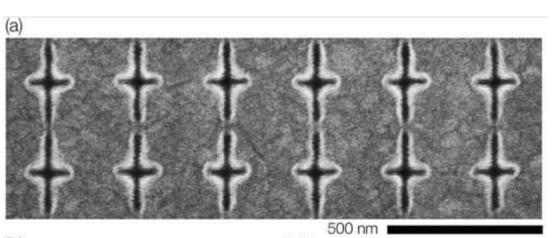
Joel Yang 2012

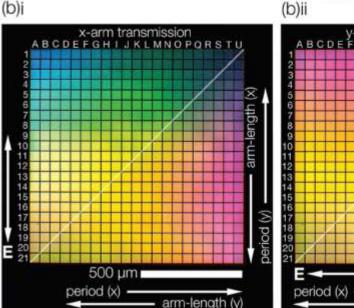
Plasmonic color printing

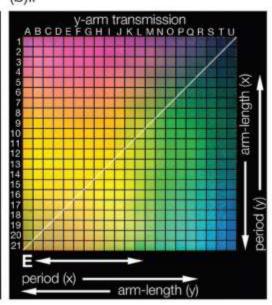


Nature Nanotechnology, 7, 557–561 (2012)

Plasmonic Dual-State Nanopixels







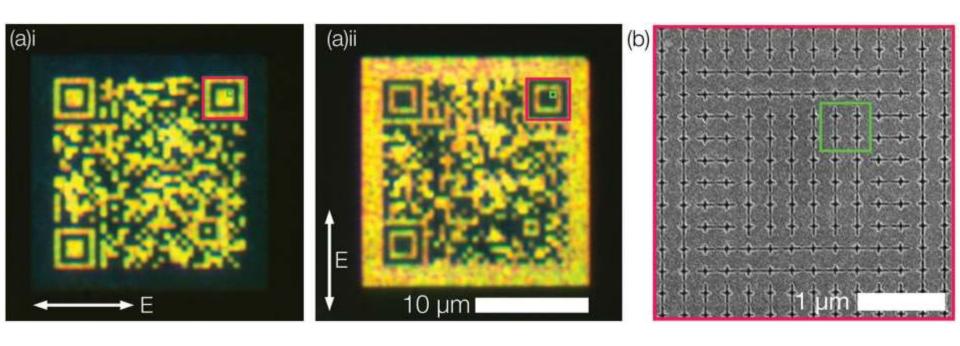
Nanofabrication using:

metal-evaporation of aluminum film electron-beam lithography reactive ion etching and inductively coupled plasma deposition



Heydari, Sperling, Neale, and Clark *Adv. Funct. Mater.* **2017**, 1701866

Switchable QR-code



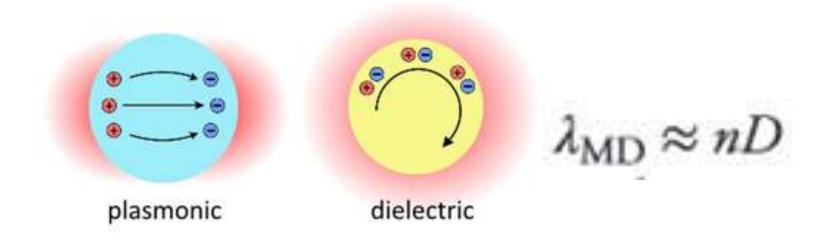
Bright-field and SEM images of a switchable QR-code



Heydari, Sperling, Neale, and Clark, Adv. Funct. Mater. 2017, 1701866

Plasmonic and All-dielectric nanophotonics

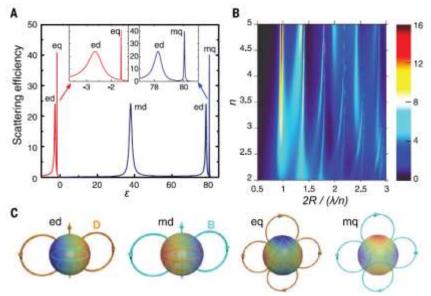
The spectral position of the MD resonance of a spherical particle is approximately defined by $\lambda_{\text{MD}} \approx nD$ with n being the refractive index of the sphere and D its diameter



Baranov, ..., Evlyukhin, Chichkov

Optica, Vol. 4, Issue 7, pp. 814-825 (2017)

Dielectric photonics

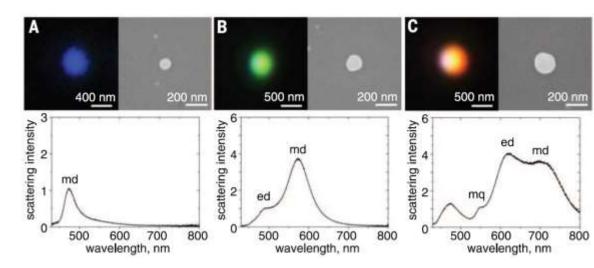


Resonant dielectric nanostructures

Kuznetsov, Miroshnichenko, Brongersma, Kivshar & Luk'yanchuk, Science 2016

Mie resonances

of a spherical particle



Materials for dielectric photonics

Crystalline and amorphous Silicon n~3.5 in the visible and near IR range

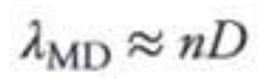
Low losses

Cheap

Robust

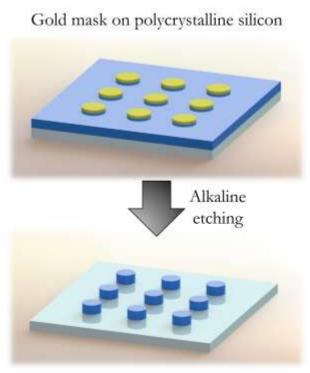
Chemically stable

Compatible with microelectronic processing

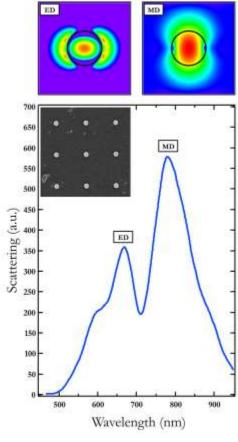


Amorphous Si resonators





Silicon resonators on glass

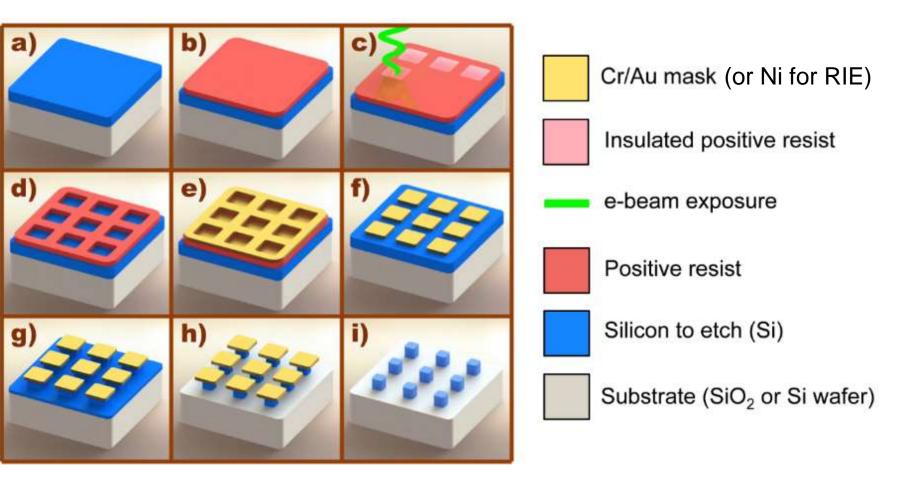


Chemical Alkaline Etching of Silicon Mie Particles

Julien Proust,* Frédéric Bedu, Stéphane Chenot, Ibrahima Soumahoro, Igor Ozerov, Bruno Gallas, Redha Abdeddaim, and Nicolas Bonod*

Advanced Optical Materials, 3, 1280–1286, Septembre 2015

Nanofabrication of silicon structures



WET ALCALINE or PLASMA RIE

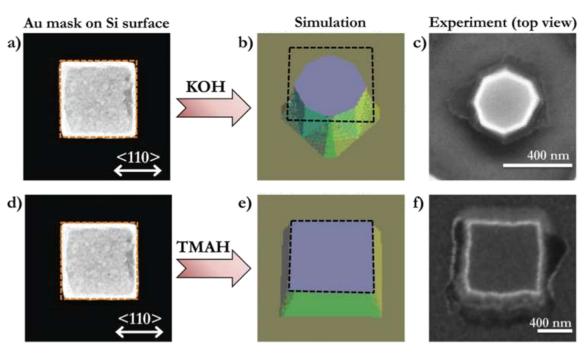
Control of the nanostructure shape and size

Crystalline silicon nanostructures

KOH or TMAH?

KOH {110}>{100}>{111}

TMAH {100}>{110}>{111}

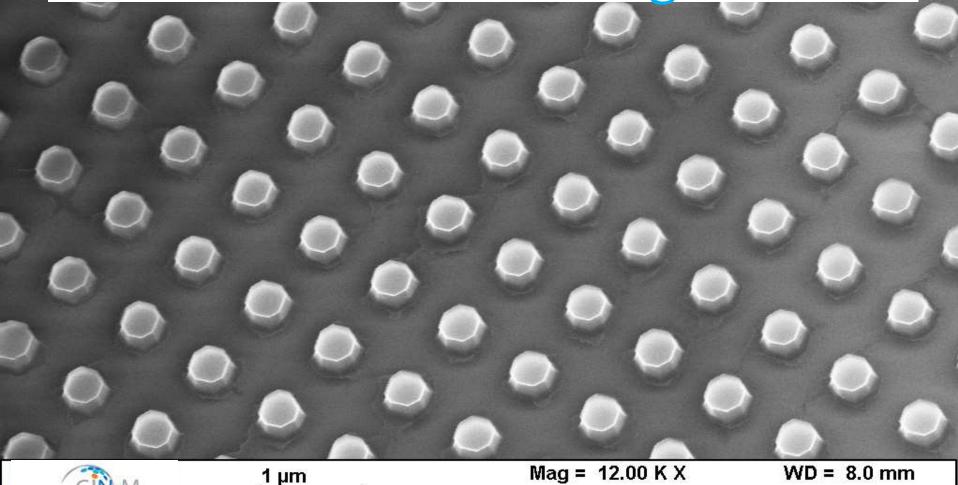


Selective chemical etching, Cr/Au mask



J. Proust, F. Bedu, S. Chenot, I. Soumahoro, I. Ozerov, B. Gallas, R. Abdeddaim, and N. Bonod, Advanced Optical Materials, vol. 3, pp. 1280-1286, 2015.

Crystalline silicon nanostructures Alcaline etching



InLens

EHT = 10.00 kV

Crystalline silicon nanostructures Alcaline etching

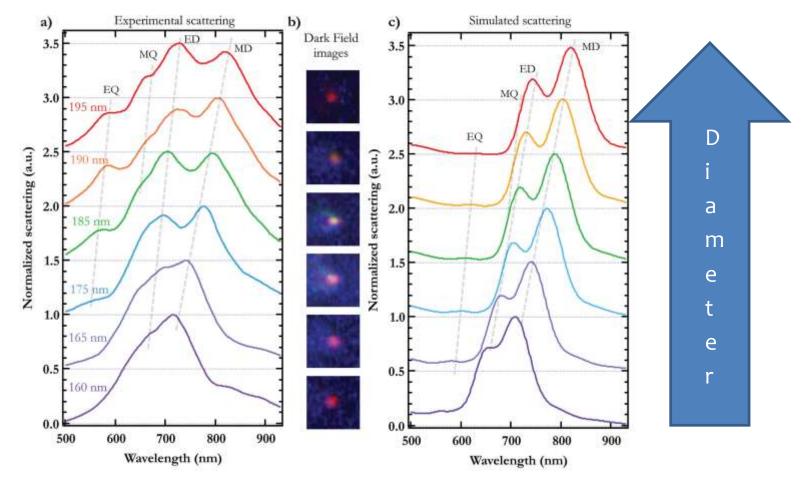


1 µm

Mag = 12.00 K X InLens

WD = 8.0 mm EHT = 10.00 kV

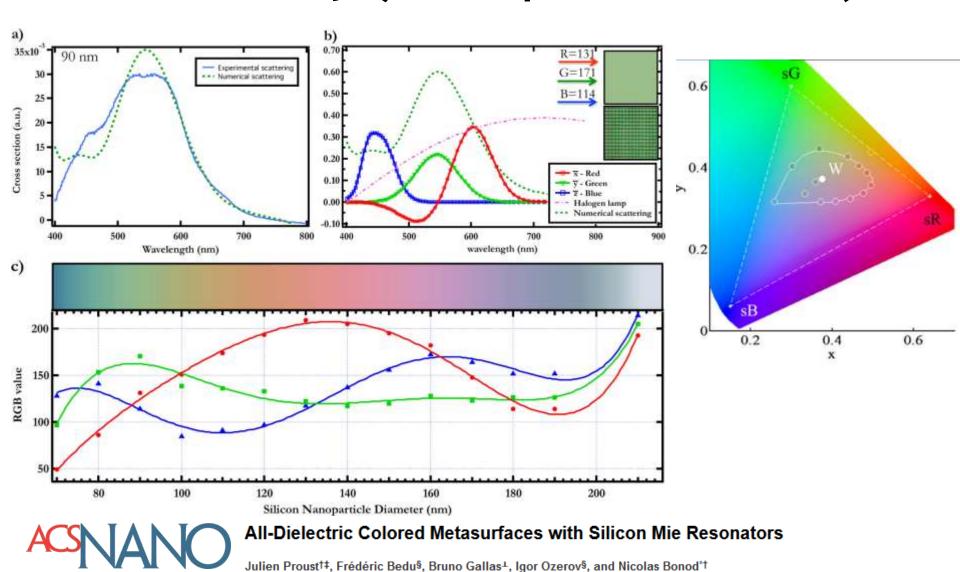
Scattering from individual Si particles





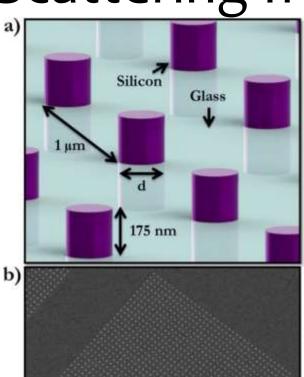
2015 Proust, Bedu, Chenot, Soumahoro, Ozerov, Gallas, Abdeddaim, and Bonod

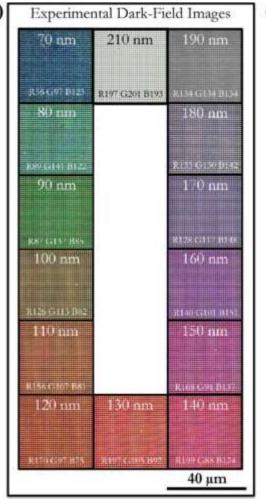
Colometry (amorphous silicon)

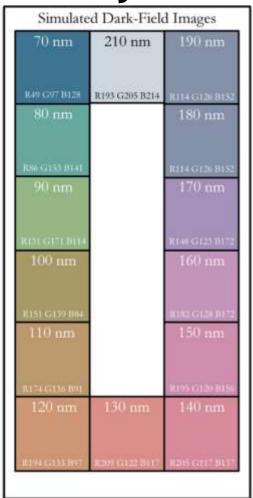


Igor OZEROV

Scattering from individual Si cylinders









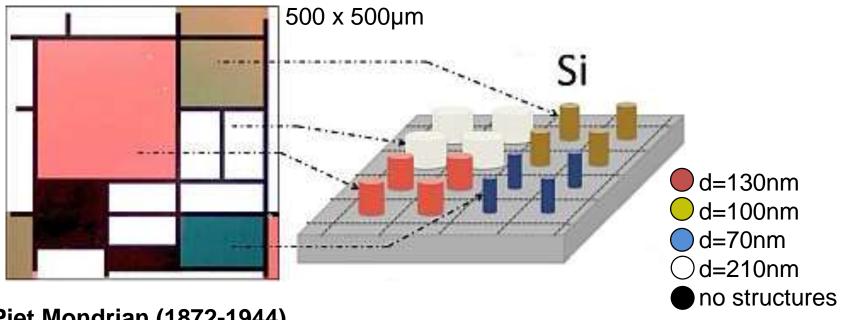
All-Dielectric Colored Metasurfaces with Silicon Mie Resonators

Julien Proust†‡, Frédéric Bedu§, Bruno Gallas±, Igor Ozerov§, and Nicolas Bonod*†

10 µm

Amorphous silicon structures for nanoscale painting

Dark Field Microscopy

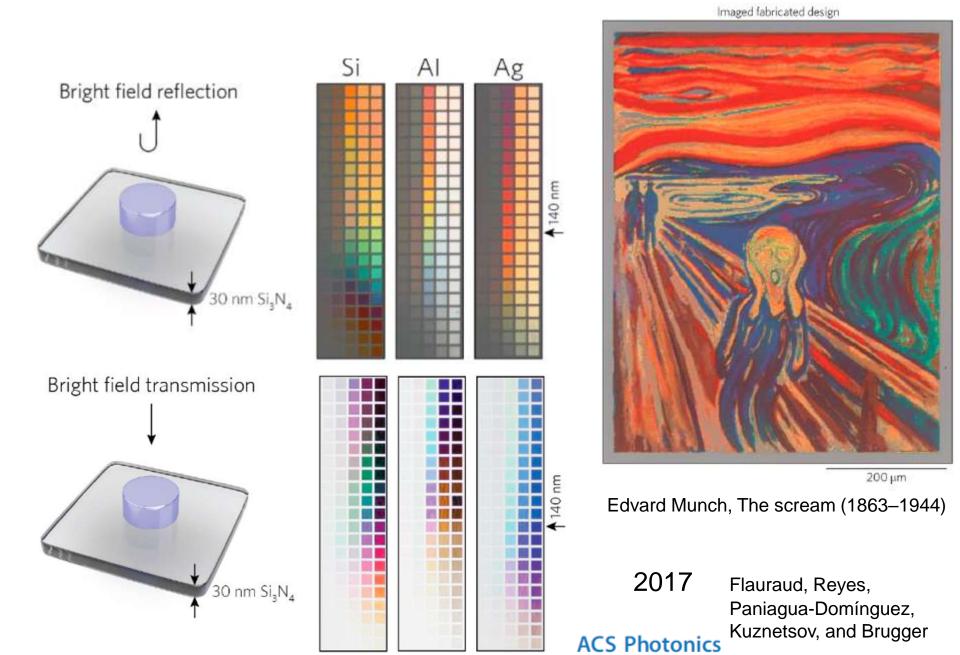


Piet Mondrian (1872-1944)



All-Dielectric Colored Metasurfaces with Silicon Mie Resonators

Julien Proust†‡, Frédéric Bedu§, Bruno Gallas±, Igor Ozerov§, and Nicolas Bonod*†



Black Silicon Antireflective Coating

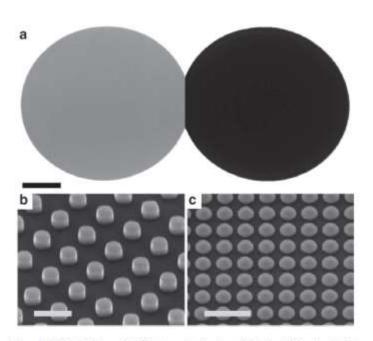
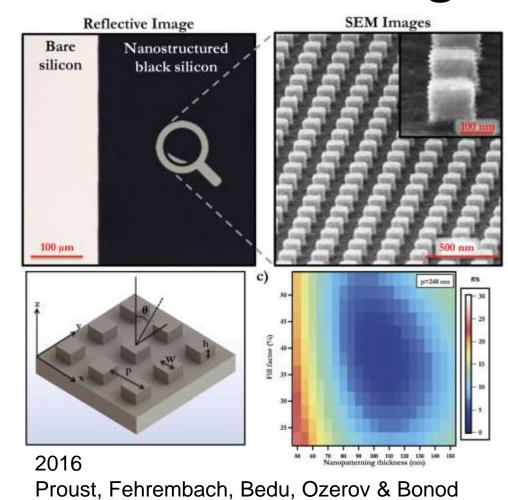


Figure 3 | Black silicon. (a) Photograph of a bare flat 4-inch Si wafer (left) and a 4-inch Si wafer fully imprinted with an optimized (250 nm diameter, 150 nm height, 450 nm pitch) Si NP array and overcoated with a 60-nm-thick Si_3N_4 layer (right). Scale bar represents 1 inch. (b) Scanning electron microscopy image taken under an angle of 40° of a bare Si NP array (scale bar represents 500 nm) and (c) a Si NP array coated with a 60-nm-thick Si_3N_4 layer (scale bar represents 1 μ m).

2011 Spinelli, Verschuuren & Polman

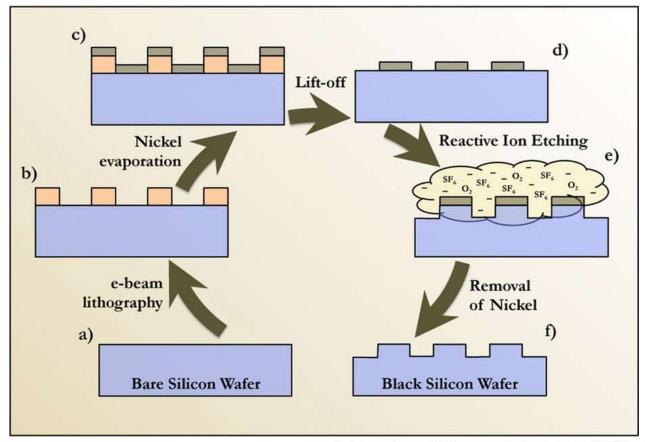




SCIENTIFIC REPORTS

DOI: 10.1038/srep24947

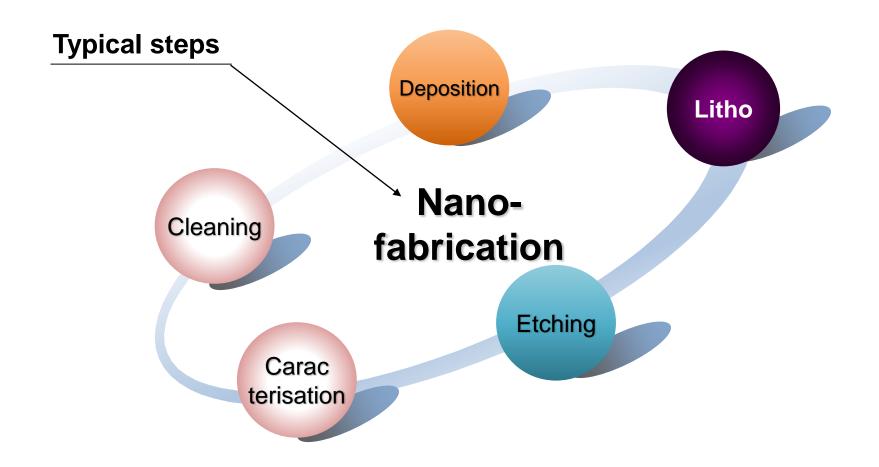
Black Silicon Antireflective Coating nanofabrication steps





DOI: 10.1038/srep24947

Top-Down Approach



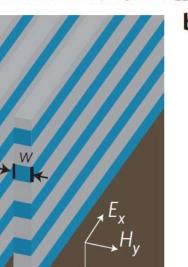
All-dielectric zero-index optical metamaterial



Realization of an all-dielectric zero-index optical metamaterial

Parikshit Moitrath, Yuanmu Yangth, Zachary Anderson2, Ivan I. Kravchenko3, Dayrl P. Briggs3

and Jason Valentine4*



from $\lambda = 1432$ nm to 1457 nm the permittivity is negative but the permeability remains positive

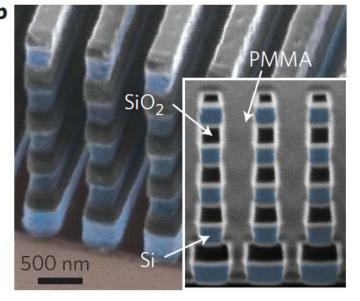
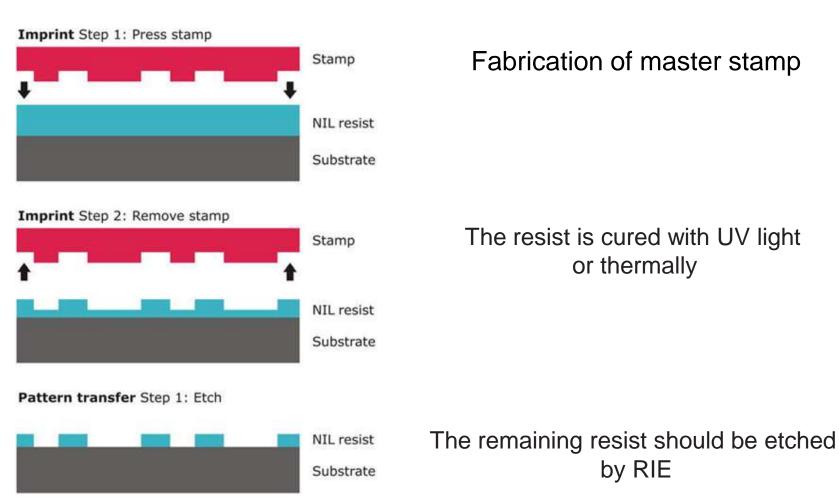


Figure 1 | Diagram and images of fabricated ZIM structure.

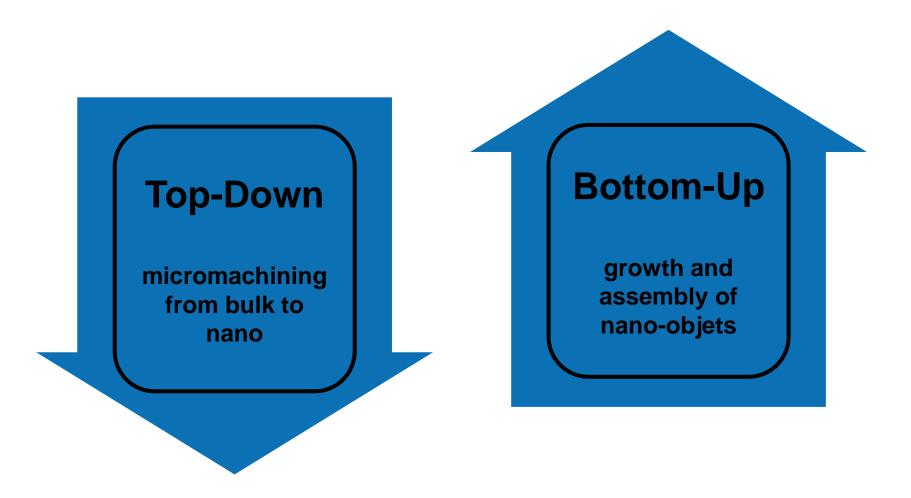
electron-beam lithography, and RIE were used to structure the multilayer film

Nanoimprint Lithography



Jung and Byun Biomed Eng Lett (2011) 1:153-162

Nano- et micro- fabrication approaches



Nanosphere Lithography

Alternative Masks for Nanolithography

The Open Physical Chemistry Journal, 2007, Volume 1

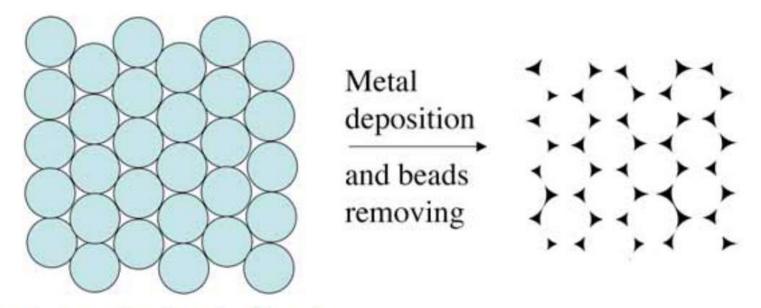
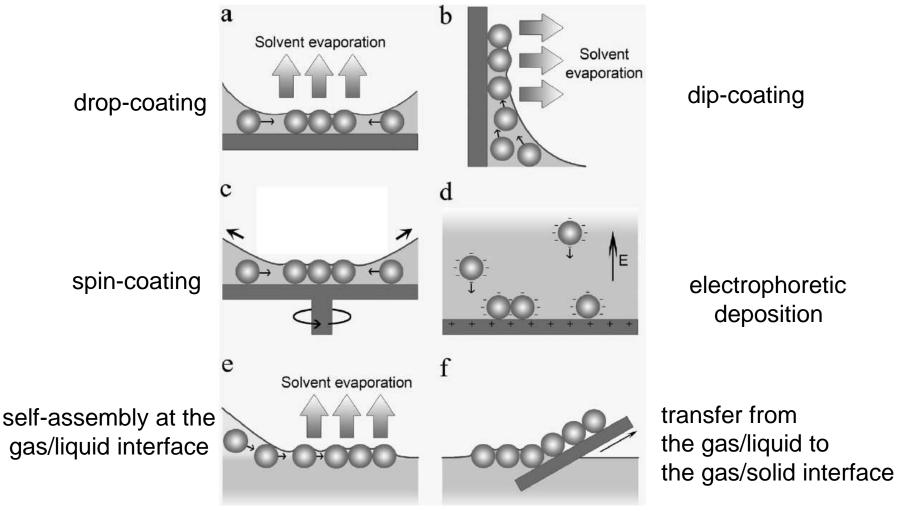


Fig. (1). Schematic representation of nanosphere lithography.

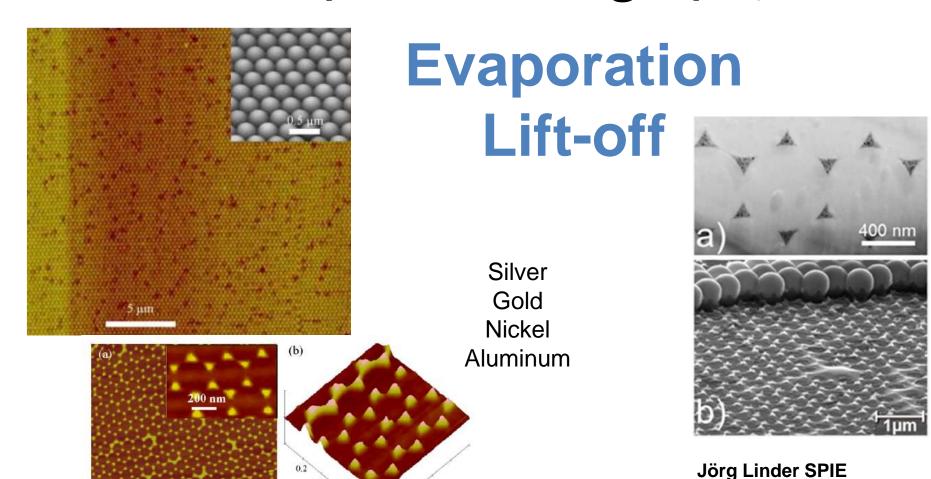
D. Ingert, 2007

Bead self-assembly strategies



Ye and Qi, Nano Today (2011) 6, 608—631

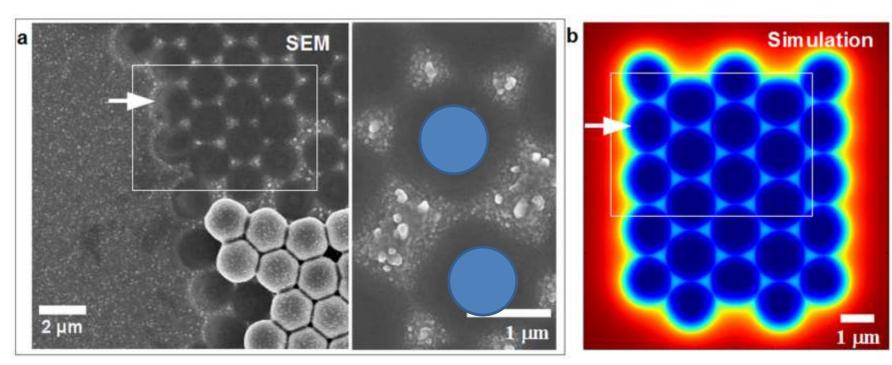
Nanosphere Lithography



Y. Song, H.E. Elsayed-Ali / AppliedSurfaceScience 256 (2010) 5961–5967

10.1117/2.1201310.005154

Tuning pit-size with Al thickness



Sputtering & Lift-off

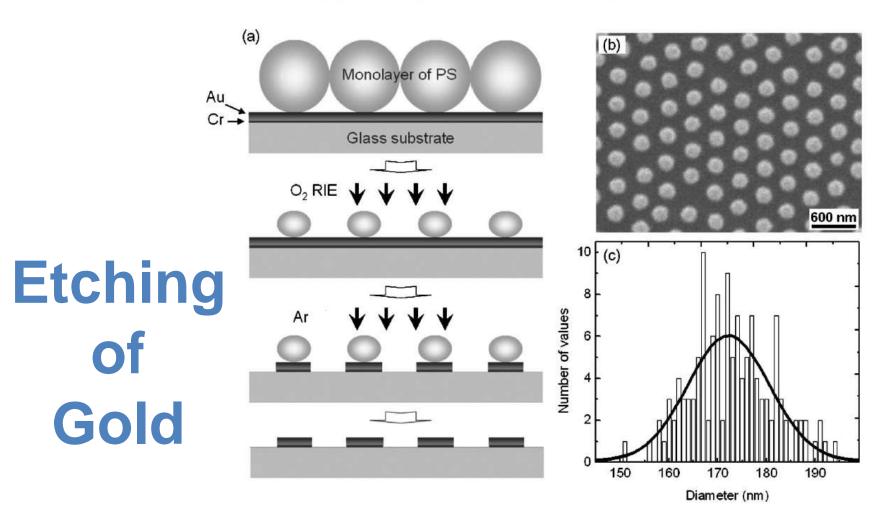


Pi, Dillard, Alameddine, Benard, Wahl, Ozerov, Charrier, Limozin, Sengupta, Nano Letters, 15, 5178–5184 (2015)

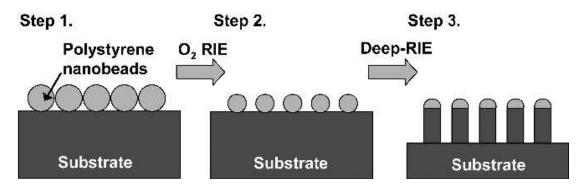


Nanosphere Lithography

Zheng et al. J. Appl. Phys. 103, 014308 (2008)

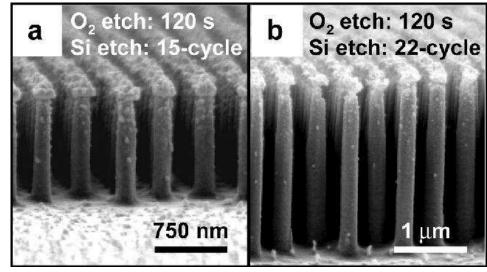


Fabrication of nanopillars by nanosphere lithography

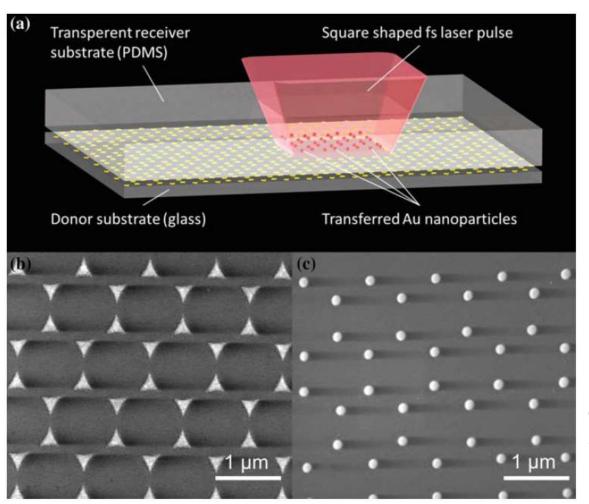


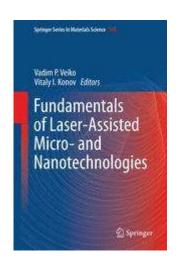
Deep Etching of Silicon

Cheung et al. Nanotechnology **17** (2006) 1339–1343



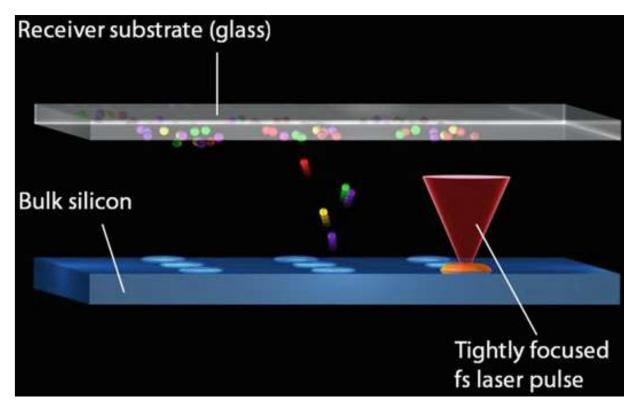
Laser Generation and Printing of Gold Nanoparticles

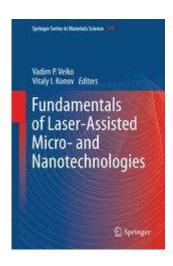




Barchanski, Evlyukhin, Koroleva, Reinhardt, Sajti, Zywietz and Chichkov 2014

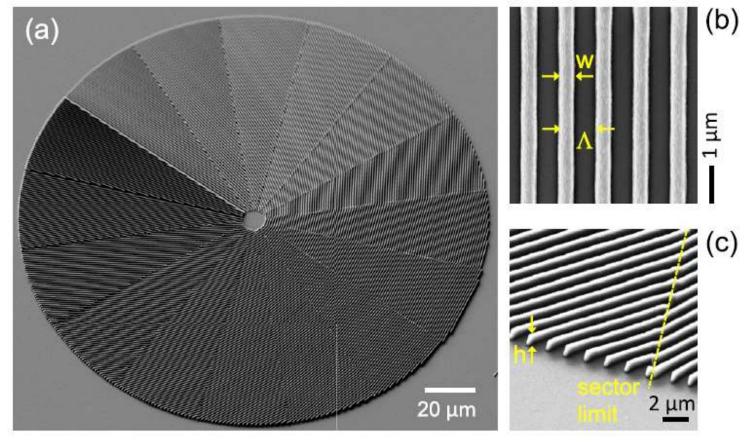
Laser Generation and Printing of Silicon Nanoparticles





Barchanski, Evlyukhin, Koroleva, Reinhardt, Sajti, Zywietz and Chichkov 2014

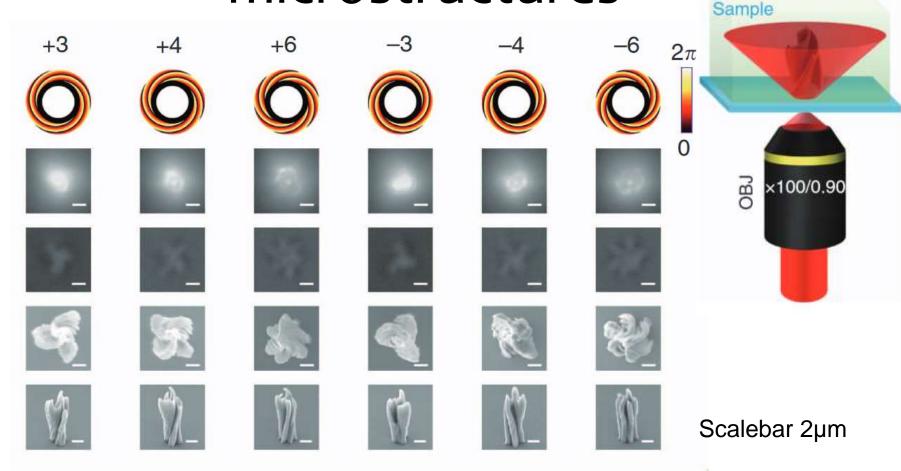
Photopolymerisation direct laser writing in photoresists



geometric phase optical elements

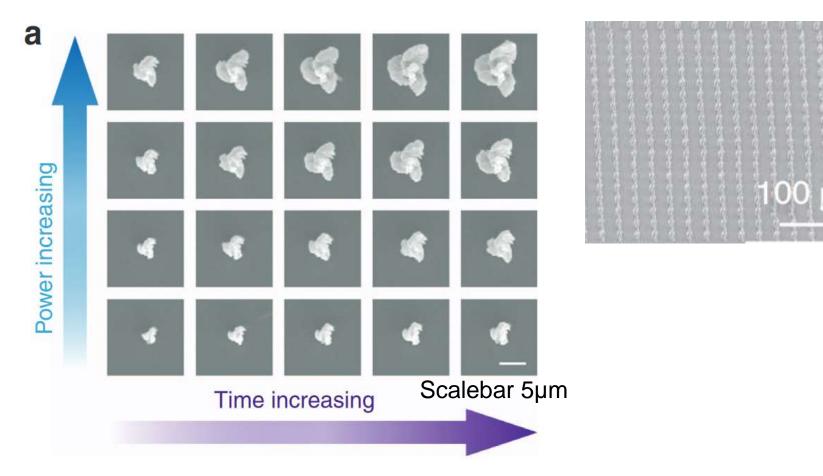
Wang et al. Appl. Phys. Lett. 110, 181101 (2017)

Laser-assisted fabrication of 3D chiral microstructures



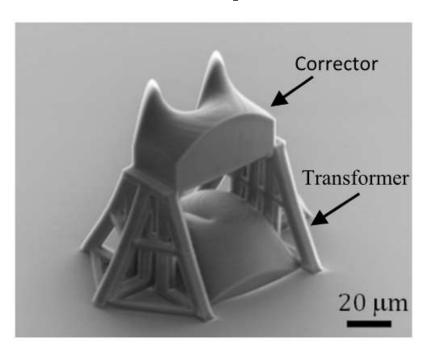
J. Ni et al. Light: Science & Applications (2017) 6, e17011

Laser-assisted fabrication of 3D chiral microstructures



J. Ni et al. Light: Science & Applications (2017) 6, e17011

Mode sorter for vortex beams produced by 3D laser printing



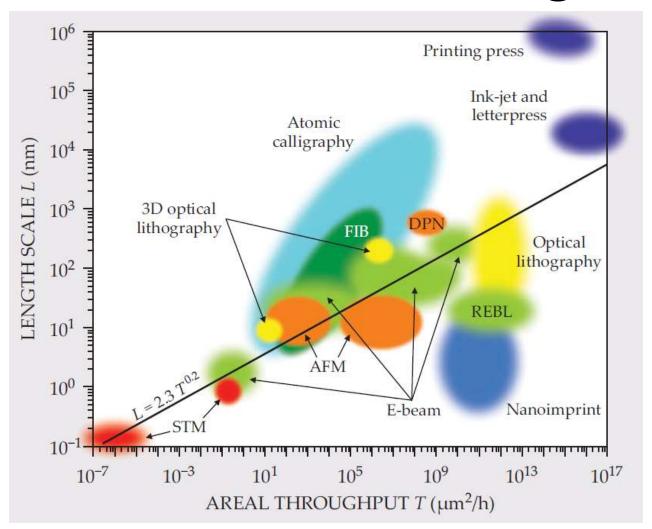
LIGHTMAN et al., Optica 4 (2017) 605

Fig. 1. Top: Theoretical (de)multiplexer designs of the (a) transforming and (b) correcting elements. Bottom: (c, d) SEM images of the above-fabricated elements. Scale bars are 25 μ m.

S. Lightman et al. Optica (2017) 4, 6051

Scalebar 25µm

Nanomanufacturing



Imboden and Bishop, **Top-down nanomanufacturing**, Physics Today **67**, 45 (2014)

Conclusions

Nanofabrication deals with

Precision

Resolution

Process Speed

Area to be treated

Cost

2D layer by layer or 3D direct writing

Sometimes low-cost bottom-up methods give excellent results

Acknowledgements





Frédéric BEDU



Benjamin DEMIRDJIAN





Julien PROUST





Yeon Ui LEE



Jeong Weon WU





Nicolas BONOD

Thank you for your attention!